

ABSTRACT OF THE DISCLOSURE

The ferroelectric memory device has a plurality of capacitor elements each formed on a semiconductor substrate and composed of a lower electrode, a capacitor insulating film made of a ferroelectric material formed on the lower electrode, and an upper electrode formed on the capacitor insulating film. Each of the lower electrodes is buried in a burying insulating film to have an upper surface planarized relative to the upper surface of the burying insulating film and has a plane configuration such that the distance from an arbitrary position on the upper surface of the lower electrode to the nearest end portion thereof is 0.6 μm or less.